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74LVTH16501 Low Voltage 18-Bit Universal Bus Transceivers with Bushold and 3-STATE Outputs

General Description

The LVTH16501 is an 18-bit universal bus transceiver combining D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in <u>each</u> direction is controlled by output-enable (OEAB and OEBA), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs.

The LVTH16501 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

The transceiver is designed for low voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVTH16501 is fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

Features

- \blacksquare Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- Eive insertion/extraction permitted
 Power up/down high impedance provides glitch-free bus
- loading
- Outputs source/sink –32 mA/+64 mA
- Functionally compatible with the 74 series 16501
- ESD Performance: Human-Body Model > 2000V Machine Model > 200V
 - Charged-Device Model > 1000V

Ordering Code:

Order Number	Package Number	Package Description			
74LVTH16501MEA	MS56A	56-Lead Shrink Small Outline Package (SSOP), JEDEC MO-118, 0.300 Wide			
74LVTH16501MTD	MTD56	56-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide			
Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.					



Connection Diagram						
Connection D OEAB - LEAB - A1 GND - A2 - A3 - Vcc - A4 - A5 - GND - A7 - A9 - A9 - A9 - A9 - A9 - A1 - A9 - A1 - A9 - A1 - A9 - A1 -	1 56 2 55 3 54 4 55 5 52 6 51 7 50 8 49 9 48 10 47 11 46 12 45 13 44 14 43 15 42 16 41 17 40 18 39 19 38 20 37 21 36 22 35 23 34 24 33 25 32 26 37 27 30	$ \begin{array}{c} GND \\ CLKAE \\ B_1 \\ GND \\ B_2 \\ B_3 \\ V_{CC} \\ B_4 \\ B_5 \\ GND \\ B_6 \\ GND \\ B_7 \\ B_8 \\ B_9 \\ B_{10} \\ B_{11} \\ B_{12} \\ GND \\ B_{13} \\ B_{14} \\ S_{16} \\ CLKBA \\ \end{array} $				
LEBA —	28 29	— GND				

Functional Description

For A-to-B data flow, the device operates in the transparent mode when LEAB is HIGH. When LEAB is LOW, the A data is latched if CLKAB is held at a HIGH or LOW logic level. If LEAB is LOW, the A bus data is stored in the latch/ flip-flop on the LOW-to-HIGH transition of CLKAB. Outputenable OEAB is active-HIGH. When OEAB is HIGH, the

Logic Diagram

Pin Descriptions

Pin Names	Description
A ₁ -A ₁₈ B ₁ -B ₁₈	Data Register A Inputs/3-STATE Outputs
B ₁ -B ₁₈	Data Register B Inputs/3-STATE Outputs
CLKAB, CLKBA	Clock Pulse Inputs
LEAB, LEBA	Latch Enable Inputs
OEAB, OEBA	Output Enable Inputs

Function Table (Note 1)

	Output			
OEAB	LEAB	CLKAB	A _n	B _n
L	Х	Х	Х	Z
Н	Н	Х	L	L
н	н	Х	н	н
н	L	\uparrow	L	L
н	L	\uparrow	н	н
н	L	н	х	B ₀ (Note 2)
н	L	L	Х	B ₀ (Note 3)
H = HIGH Volta	age Level	I = I OW	Voltage Lev	el

Z = High Impedance X = Immaterial

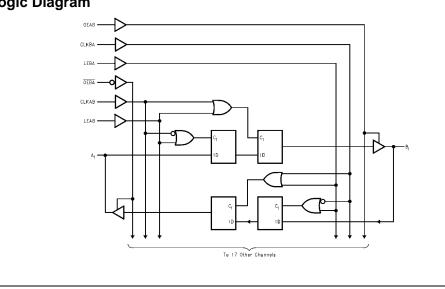
 \uparrow = LOW-to-HIGH Clock Transition

Note 1: A-to-B data flow is shown: B-to-A flow is similar but uses \overline{OEBA} , LEBA, and CLKBA. \overline{OEBA} is active LOW

Note 2: Output level before the indicated steady-state input conditions were established, provided that CLKAB was HIGH before LEAB went LOW. Note 3: Output level before the indicated steady-state input conditions were established.

outputs are active. When OEAB is LOW, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A-to-B but uses OEBA, LEBA, and CLKBA. The output enables are complementary (OEAB is active-HIGH and OEBA is active-LOW).



Absolute Maximum Ratings(Note 4)

Symbol	Parameter	Value	Conditions	Units
V _{CC}	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in HIGH or LOW State (Note 5)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{ОК}	DC Output Diode Current	-50	V _O < GND	mA
I _O	DC Output Current	64	V _O > V _{CC} Output at HIGH State	mA
		128	V _O > V _{CC} Output at LOW State	ША
I _{CC}	DC Supply Current per Supply Pin	±64		mA
I _{GND}	DC Ground Current per Ground Pin	±128		mA
T _{STG}	Storage Temperature	-65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I _{OH}	HIGH-Level Output Current		-32	mA
I _{OL}	LOW-Level Output Current		64	mA
T _A	Free-Air Operating Temperature	-40	85	°C
$\Delta t/\Delta V$	Input Edge Rate, $V_{IN} = 0.8V-2.0V$, $V_{CC} = 3.0V$	0	10	ns/V

Note 4: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 5: I_O Absolute Maximum Rating must be observed.

Symbol	Parameter		V _{CC}	T _A = -40° C to $+85^{\circ}$ C		Units	Conditions
Symbol	Faialletei	rarameter		Min	Max	Units	
V _{IK}	Input Clamp Diode Voltage		2.7		-1.2	V	I _I = -18 mA
VIH	Input HIGH Voltage		2.7–3.6	2.0		V	$V_0 \le 0.1V$ or
VIL	Input LOW Voltage		2.7–3.6		0.8	v	$V_O \geq V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage		2.7–3.6	V _{CC} - 0.2		V	$I_{OH} = -100 \ \mu A$
			2.7	2.4		V	I _{OH} = -8 mA
			3.0	2.0		V	I _{OH} = -32 mA
V _{OL}	Output LOW Voltage		2.7		0.2	V	I _{OL} = 100 μA
			2.7		0.5	V	I _{OL} = 24 mA
		Γ	3.0		0.4	V	I _{OL} = 16 mA
		ľ	3.0		0.5	V	I _{OL} = 32 mA
			3.0		0.55	V	I _{OL} = 64 mA
I _{I(HOLD)}	Bushold Input Minimum Drive		3.0	75		μA	$V_I = 0.8V$
			5.0	-75		μA	$V_{I} = 2.0V$
I _{I(OD)}	Bushold Input Over-Drive Current to Change State		3.0	500		μA	(Note 6)
			3.0	-500		μA	(Note 7)
l _l	Input Current		3.6		10	μA	$V_{I} = 5.5V$
	Co	ontrol Pins	3.6		±1	μΑ	$V_I = 0V \text{ or } V_{CC}$
	D	ata Pins	3.6		-5	μΑ	$V_I = 0V$
		ala F 1115	5.0		1	μA	$V_I = V_{CC}$
I _{OFF}	Power Off Leakage Current		0		±100	μΑ	$0V \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$
I _{PU/PD}	Power up/down 3-STATE		0–1.5V		±100	μA	$V_0 = 0.5V \text{ to } 3.0V$
	Output Current		0-1.51		±100	μΑ	$V_I = GND \text{ or } V_{CC}$
I _{OZL}	3-STATE Output Leakage Current		3.6		-5	μA	$V_{0} = 0.0V$
I _{OZH}	3-STATE Output Leakage Current		3.6		5	μA	V _O = 3.6V
I _{OZH} +	3-STATE Output Leakage Current		3.6		10	μΑ	$V_{CC} < V_O \le 5.5V$
I _{CCH}	Power Supply Current		3.6		0.19	mA	Outputs HIGH
I _{CCL}	Power Supply Current		3.6		5	mA	Outputs LOW
I _{CCZ}	Power Supply Current		3.6		0.19	mA	Outputs Disabled

Note 8: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Note 6: An external driver must source at least the specified current to switch from LOW-to-HIGH. Note 7: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Dynamic Switching Characteristics (Note 9)

Increase in Power Supply Current

(Note 8)

Symbol	Parameter	Vcc	T _A = 25°C			Units	Conditions	
Symbol	Falameter	(V)	(V) Min		Max	Units	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 10)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 10)	

0.2

mΑ

3.6

Outputs Disabled

One Input at V_{CC} – 0.6V

Other Inputs at V_{CC} or GND

Note 9: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 10: Max number of outputs defined as (n). n–1 data inputs are driven 0V to 3V. Output under test held LOW.

 ΔI_{CC}

			T _A = -40	t _L = 500 Ω			
Symbol	Parar	neter	V _{CC} = 3	$.3\pm0.3V$	V _{CC} =	$V_{CC} = 2.7V$	
		Min	Max	Min	Max		
f _{MAX}	CLKAB or CLKBA to B or A		150		150		MHz
t _{PLH}	Propagation Delay	1.3	5.1	1.3	5.6	ns	
t _{PHL}	Data to Outputs		1.3	4.7	1.3	5.3	115
t _{PLH}	Propagation Delay	1.5	5.5	1.5	6.1	ns	
t _{PHL}	LEBA or LEAB to B or A	1.5	5.1	1.5	5.7	115	
t _{PLH}	Propagation Delay	1.3	56	1.3	6.2	ns	
t _{PHL}	CLKBA or CLKAB to B or A	1.3	5.1	1.3	5.7	115	
t _{PZH}	Output Enable Time	1.3	4.9	1.3	5.6	ns	
t _{PZL}		1.3	5.4	1.3	6.2	115	
t _{PHZ}	Output Disable Time		1.7	5.9	1.7	6.6	ns
t _{PLZ}			1.7	5.8	1.7	6.3	115
t _S	Setup Time	A before CLKAB	2.1		2.4		
		B before CLKBA	2.1		2.4		ns
		A or B before LE, CLK HIGH	2.4		1.6		115
		A or B before LE, CLK LOW	2.4		1.6		
t _H	Hold Time	A or B after CLK	1.0		1.0		ns
		A or B after LE	1.7		1.7		115
t _W	Pulse Width	LE HIGH	3.3		3.3		ns
		CLK HIGH or LOW	3.3		3.3		
t _{OSLH}	Output to Output Skew (Note 11)			1.0		1.0	ns
tOSHL				1.0		1.0	115

Note 11: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}).

Capacitance (Note 12)

Symbol	Parameter	Conditions	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.0V, V_O = 0V \text{ or } V_{CC}$	8	pF
Note 12: Ca	pacitance is measured at frequency f - 1 MHz per	MIL-STD-883 Method 3012		

is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.

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